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**2224/40225** (2013.01)(57) **ABSTRACT**

Provided is a semiconductor device. A semiconductor device is implemented as a semiconductor module package for driving an inverter, the semiconductor device may include: a first upper metal layer in which a plurality of semiconductor chips implementing a right phase switching pattern are disposed along a first direction to form a first row; a second upper metal layer in which a plurality of semiconductor chips implementing a left phase switching pattern are disposed along the first direction to form a second row; a first connection, in the first upper metal layer, connecting a plurality of semiconductor chips disposed along the first row to each other in series and to the second upper metal layer in parallel; and a second connection, in the second upper metal layer, connecting a plurality of semiconductor chips disposed along the second row to each other in series.

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